# VS-25RIA Series

**Vishay Semiconductors** 

# Medium Power Phase Control Thyristors (Stud Version), 25 A



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PRODUCT SUMMARY				
Package	TO-208AA (TO-48)			
Diode variation	Single SCR			
I <sub>T(AV)</sub>	25 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V to 1200 V			
V <sub>TM</sub>	1.70 V			
I <sub>GT</sub>	60 mA			
Т <sub>Ј</sub>	-65 °C to 125 °C			

## FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
		25	А				
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C				
I <sub>T(RMS)</sub>		40	A				
1	50 Hz	420	•				
I <sub>TSM</sub>	60 Hz	440	A				
l <sup>2</sup> t	50 Hz	867	A <sup>2</sup> s				
1-1	60 Hz	790	A-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V				
t <sub>q</sub>	Typical	110	μs				
TJ		-65 to 125	°C				

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE	RATINGS					
TYPE NUMBER	VOLTAGE CODE			$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA		
	10	100	100 150			
	20	200	300			
	40	400	500			
VS-25RIA	60	600	700	10		
	80	800	900	10		
	100	1000	1100			
	120	1200	1300			

#### Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $^{(2)}$  For voltage pulses with  $t_p \leq 5\mbox{ ms}$ 

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PARAMETER	SYMBOL		TEST COND	DITIONS	VALUES	UNITS
Maximum average on-state current	1	180° sinusoidal conduction		25	А	
at case temperature	I <sub>T(AV)</sub>	160 Sinusoi	dai conduction		85	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				40	А
		t = 10 ms	No voltage		420	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		440	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		350	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	370	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	867	A <sup>2</sup> s
		t = 8.3 ms	reapplied		790	
		t = 10 ms	100 % V <sub>BBM</sub>		615	
		t = 8.3 ms	reapplied		560	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10 T <sub>J</sub> = T <sub>J</sub> maxi	ms, no voltage r mum	reapplied,	8670	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x I$	<sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum	0.99	v
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	, T <sub>J</sub> = T <sub>J</sub> maximu	ım	1.40	v
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			10.1	
High level value of on-state slope resistance	r <sub>t2</sub>	(I > $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			5.7	mΩ
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 79 A, T <sub>J</sub> = 25 °C			1.70	V
Maximum holding current	Ι <sub>Η</sub>	т об об о		( registive load	130	
Latching current	١L	$I_{\rm J} = 25$ °C, a	anode supply 6 V	r, resistive load	200	mA

SWITCHING									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
	$V_{DRM} \leq 600 \ V$			200					
Maximum rate of rise	$V_{DRM} \leq 800 \ V$	$dl/dt$ Gate pulse = 20 V, 15 $\Omega$ , t <sub>p</sub> = 6 µs, t <sub>r</sub> = 0.1 µs maximum		$\frac{100 \text{ V}}{100 \text{ V}}$ dl/dt Gate pulse = 20 V, 15 $\Omega$ , t <sub>p</sub> = 6 µs, t <sub>r</sub> = 0.1 µs maximu				180	A/µs
of turned-on current	$V_{DRM} \leq 1000 \; V$				ai/at	160		Ανμs	
$V_{DRM} \le 1600 \text{ V}$				150					
Typical turn-on time		t <sub>gt</sub>	$T_J$ = 25 °C, at rated $V_{DRM}/V_{RRM}$ , $T_J$ = 125 °C	0.9					
Typical reverse recovery time		t <sub>rr</sub>	$T_{J}$ = $T_{J}$ maximum, $I_{TM}$ = $I_{T(AV)},$ $t_{p}$ $>$ 200 $\mu s,$ dl/dt = - 10 A/ $\mu s$	4	μs				
Typical turn-off time		tq	$ \begin{split} T_J = T_J \; maximum, \; I_{TM} = I_{T(AV)}, \; t_p > 200 \; \mu s, \; V_R = 100 \; V, \\ dI/dt = - \; 10 \; A/\mu s, \; dV/dt = 20 \; V/\mu s \; linear \; to \; 67 \; \% \; V_{DRM}, \\ gate \; bias \; 0 \; V \; to \; 100 \; W \end{split} $	110	60				

Note

+  $t_q$  = 10  $\mu s$  up to 600 V,  $t_q$  = 30  $\mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	100	V/µs
of off-state voltage	av/at	$T_J = T_J$ maximum linear to 67 % rated $V_{DRM}$	300 (1)	v/µs

Note

<sup>(1)</sup> Available with:  $dV/dt = 1000 V/\mu s$ , to complete code add S90 i.e. 25RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>			8.0	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_{J} = T_{J} maximum$		2.0	vv
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum		1.5	А
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
		T <sub>J</sub> = - 65 °C		90	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger current/voltage are the lowest	60	mA
		T <sub>J</sub> = 125 °C		35	
		T <sub>J</sub> = - 65 °C	value which will trigger all units	3.0	v
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	6 V anode to cathode applied	2.0	
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	I <sub>GD</sub>	$T_J = T_J$ maximum, $V_{DRM} =$ Rated value		2.0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 125	°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation		K/W	
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.35	1000	
		Non-lubricated threads	3.4 <sup>+ 0 - 10 %</sup> (30)	N⋅m	
Allowable mounting torque		Lubricated threads 23		(lbf · in)	
Approvimete weight			14	g	
Approximate weight			0.49	oz.	
Case style		See dimensions - link at the end of datasheet	TO-208AA	(TO-48)	

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.17	0.13		
120°	0.21	0.22		
90°	0.27	0.30	$T_J = T_J maximum$	K/W
60°	0.40	0.42		
30°	0.69	0.70		

Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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Fig. 1 - Current Ratings Characteristics

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Fig. 1 - Current Ratings Characteristics



Fig. 2 - On-State Power Loss Characteristics



Fig. 3 - On-State Power Loss Characteristics



Fig. 4 - Maximum Non-Repetitive Surge Current

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Fig. 6 - Forward Voltage Drop Characteristics



Fig. 7 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

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Fig. 8 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

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Device code	VS-	25	RIA	120	М	S90	
	1	2	3	4	5	6	
	1 - 2 -		hay Sen rent coc	niconduo le	ctors pro	oduct	
	3 -	Ess	ential p	art numl	ber		
	4 -	Vol	tage coo	de x 10 =	= V <sub>RRM</sub>	(see Vo	Itage Ratings table)
	5 -			d base <sup>-</sup> ase TO-		`	48) 1/4" 28UNF-2A M6 x 1
	6 -	Nor		dt: ) V/µs (s ) V/µs (s		,	1)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95333			

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# TO-208AA (TO-48)

## **DIMENSIONS** in millimeters (inches)





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